



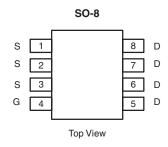
# P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
	0.011 at V <sub>GS</sub> = - 10 V	- 13.7			
- 20	0.014 at V <sub>GS</sub> = - 4.5 V	- 12.3			
	0.020 at V <sub>GS</sub> = - 2.5 V	- 10.3			

### **FEATURES**

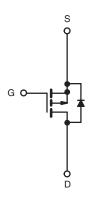
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs





Ordering Information: Si4463BDY-T1-E3 (Lead (Pb)-free)

Si4463BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 20		V
Gate-Source Voltage		V <sub>GS</sub>	± 12		
Continuous Dunis Comment /T 150 90\8	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 13.7	- 9.8	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 11.1	- 7.9	•
Pulsed Drain Current		I <sub>DM</sub>	- 50		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 2.7	- 1.36	1
M	T <sub>A</sub> = 25 °C	D.	3.0	1.5	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	- P <sub>D</sub>	1.9	0.95	**
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum boration to Ambienta	t ≤ 10 s	R <sub>thJA</sub>	35	42		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' ¹thJA	70	84	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	17	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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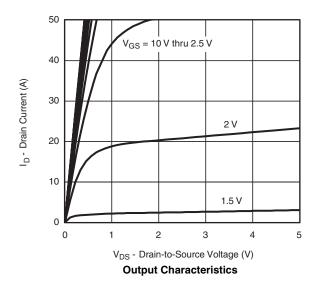
Parameter	Symbol	Test Conditions		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.6		- 1.4	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zana Cata Valtana Duain Comunit	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$			- 1	μΑ	
Zero Gate Voltage Drain Current					- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V	- 30			Α	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 13.7 A		0.0085	0.011		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 12.3 A		0.010	0.014 Ω		
		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 5 A		0.015	0.020	1	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 13.7 A		44		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 2.7 A, V <sub>GS</sub> = 0 V		- 0.7	- 1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			37	56		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -13.7 \text{ A}$		8.7		nC	
Gate-Drain Charge	$Q_{gd}$			11			
Gate Resistance	$R_g$	f = 1 MHz		2.7		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			35	55		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 10 V, $R_L$ = 10 $\Omega$		60	90		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$		115	170	ns	
Fall Time	t <sub>f</sub>			75	115		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 2.3 A, dI/dt = 100 A/μs		50	75		

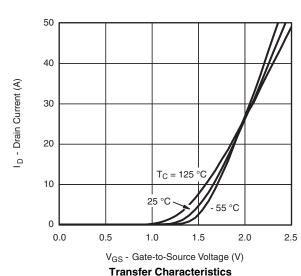
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



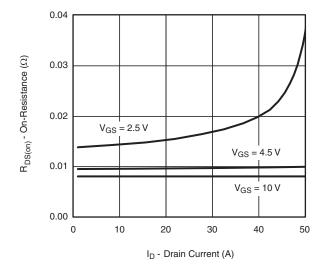




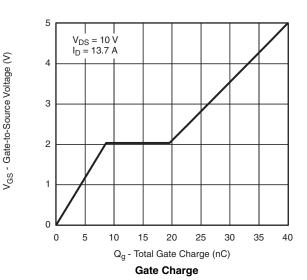




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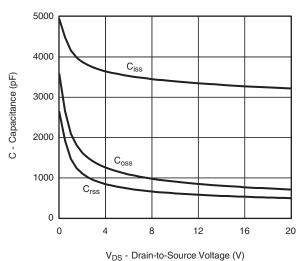


On-Resistance vs. Drain Current

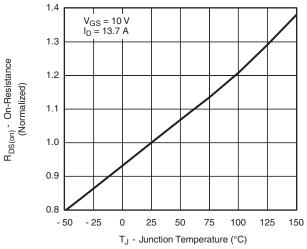


T<sub>J</sub> = 150 °C 10  $T_J = 25~^{\circ}C$ 0.0 0.2 0.4 0.6 0.8 1.0 1.2 V<sub>SD</sub> - Source-to-Drain Voltage (V)

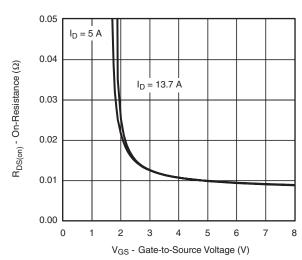
Source-Drain Diode Forward Voltage







On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

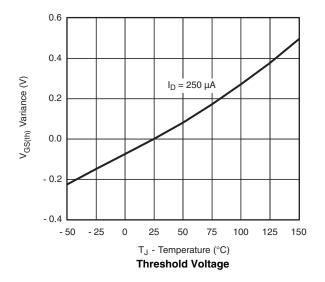
50

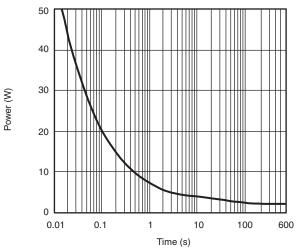
Is - Source Current (A)

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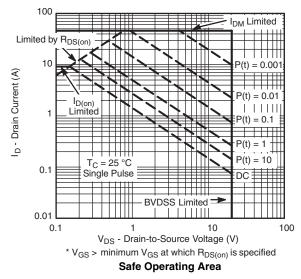
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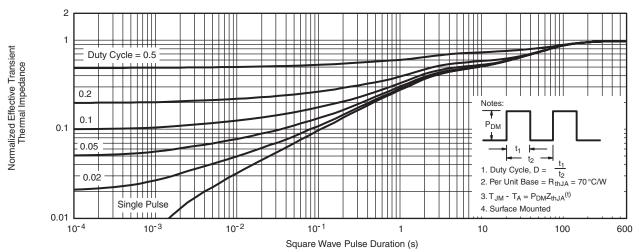
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Power, Junction-to-Ambient

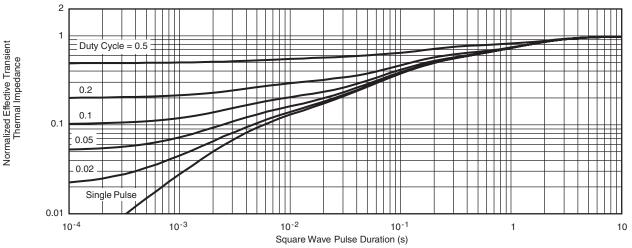




Normalized Thermal Transient Impedance, Junction-to-Ambient



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS INCHES			HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050	) BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
FCN: C-06527-Bey   11-Sen-06						

DWG: 5498

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### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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